描述 / Descriptions

N 沟道 TO-252 塑封封装场效应管。N-CHANNEL MOSFET in a TO-252 Plastic Package.

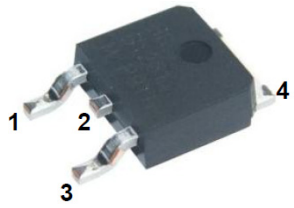
特征 / Features

RDS(on) 小，门电荷低，Crss 小，开关速度快。 无卤产品。
Low RDS(on) ,low gate charge, low Crss , fast switching. HF Product.

用途 / Applications

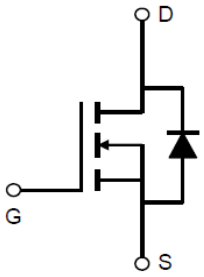
用于低压电路如：汽车电路、DC/DC 转换、便携式产品的电源高效转换、TV/Monitor 电源板卡。
Suited for low voltage applications such as automotive, DC/DC Converters, high efficiency switching for power management in portable and battery operated products,and power management interface card for TV or Monitor.

引脚排列 / Pinning



PIN1：G　　PIN 2：D　　PIN 3：S　　PIN 4：D

内部等效电路 / Equivalent Circuit



放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25℃)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	10	A
Pulsed Drain Current [C]		I_{DM}	25	
Avalanche Current [C]		I_{AS}	10.8	A
Avalanche energy L=0.1 mH [C]		E_{AS}	7	mJ
Power Dissipation [B]	T_C=25°C	P_D	54	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	44	℃/W
Maximum Junction-to-Ambient [AD]	Steady-State		110	℃/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.8	℃/W

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	150	155		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=150V, V_{GS}=0V			1	μA
		T_J=125°C			5	
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}，I_D=250μA	1		3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=7A		182	300	mΩ
		V_{GS}=4.5V, I_D=6A		183	450	
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1	V

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz		660		pF
Output Capacitance	C_{oss}			74		
Reverse Transfer Capacitance	C_{rss}			17		
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		2.6		Ω
Turn-On Delay Time	t_D(on)	V_{GS}=10V, V_{DS}=75V, I_D=5A, R_L=14.7Ω, R_{GEN}=50Ω			60	ns
Turn-On Rise Time	t_r				250	
Turn-Off Delay Time	t_D(off)				135	
Turn-Off Fall Time	t_f				135	
Body Diode Reverse Recovery Time	t_{rr}	ISD=4A, dI/dt=100A/ms		200		ns

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The
Power dissipation PDSM is based on R qJA and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

电参数曲线图 / Electrical Characteristic Curve

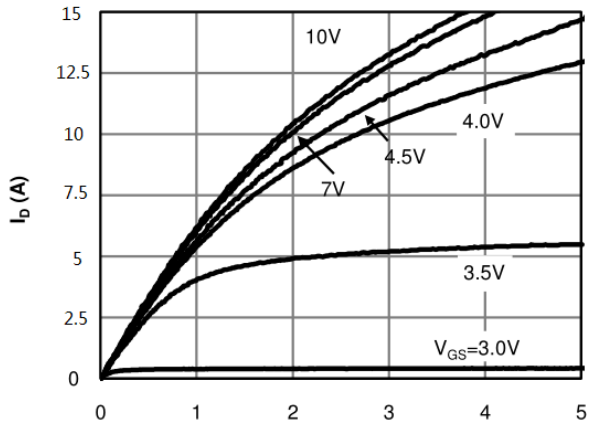


Fig 1: On-Region Characteristics

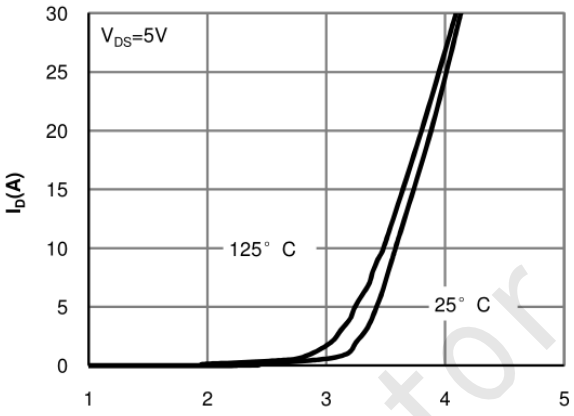


Figure 2: Transfer Characteristics

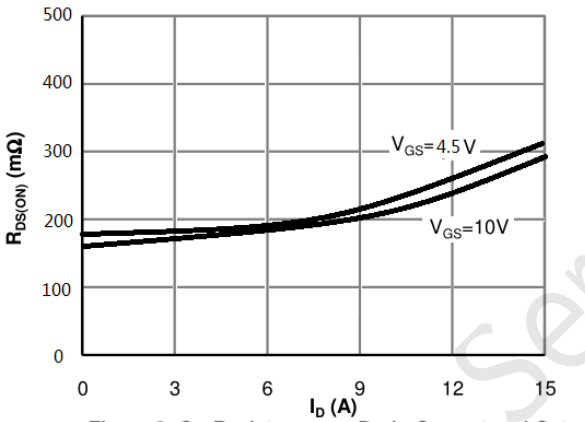


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

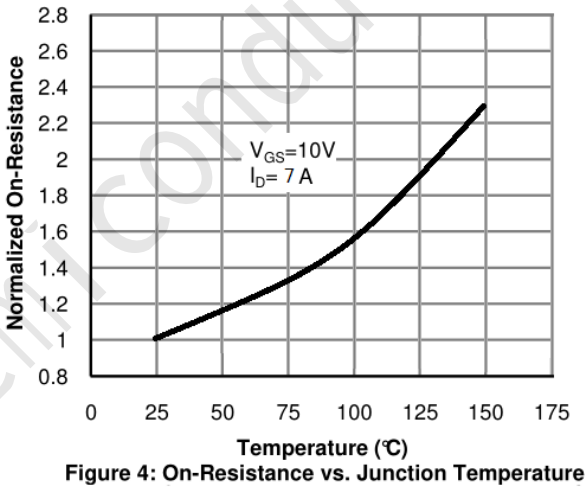


Figure 4: On-Resistance vs. Junction Temperature

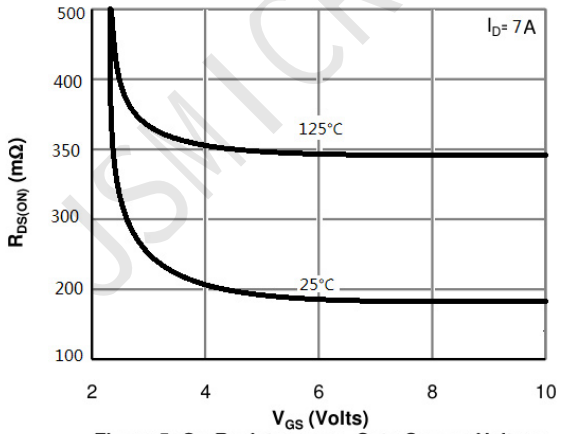


Figure 5: On-Resistance vs. Gate-Source Voltage

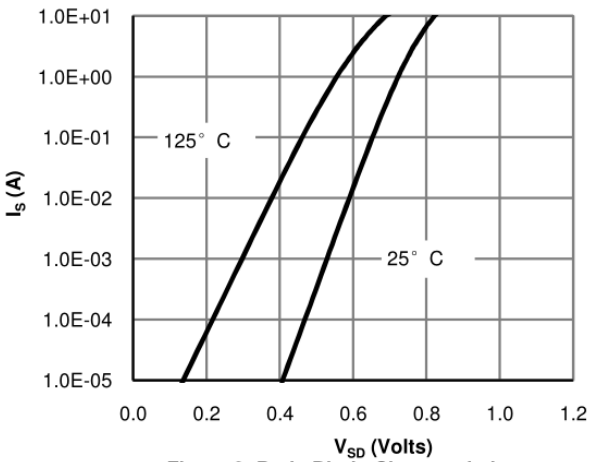


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

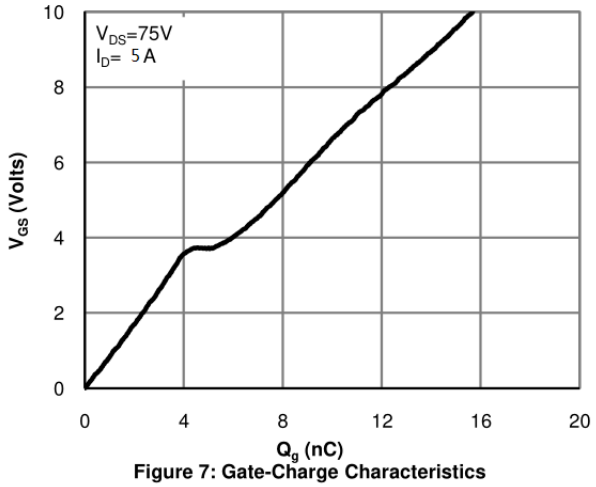


Figure 7: Gate-Charge Characteristics

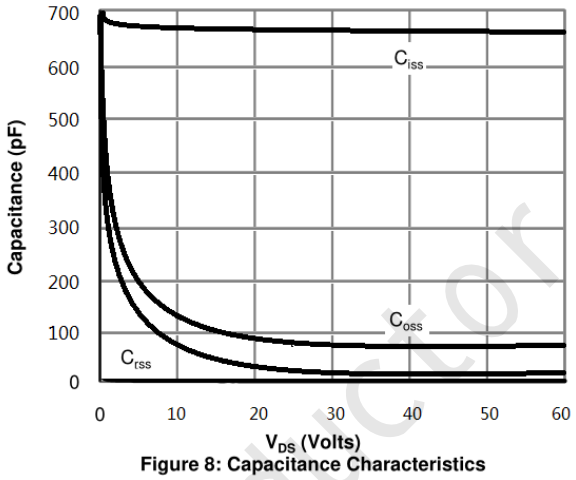


Figure 8: Capacitance Characteristics

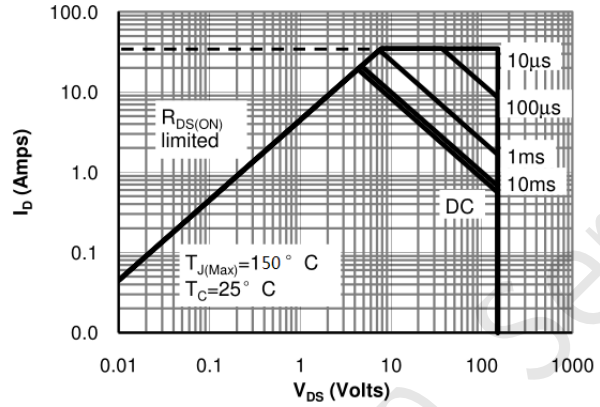


Figure 9: Maximum Forward Biased Safe Operating Area

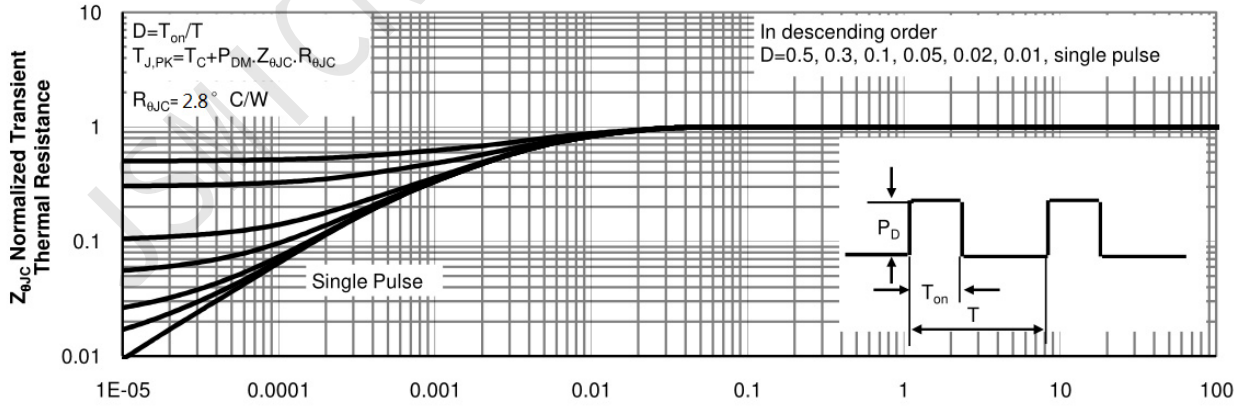
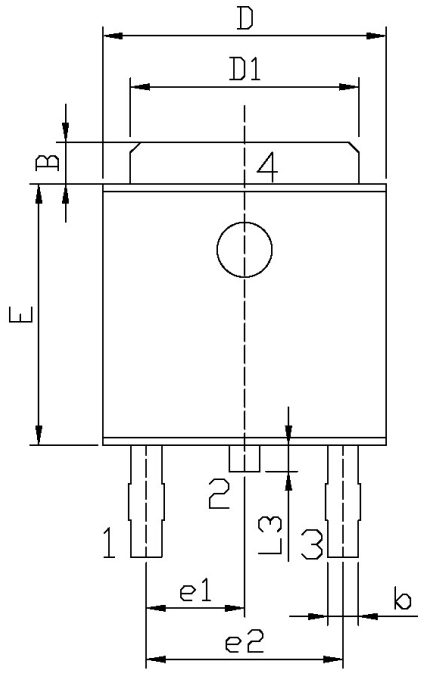
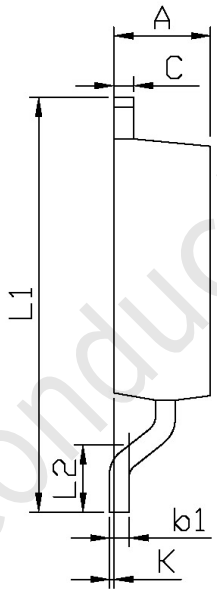


Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions



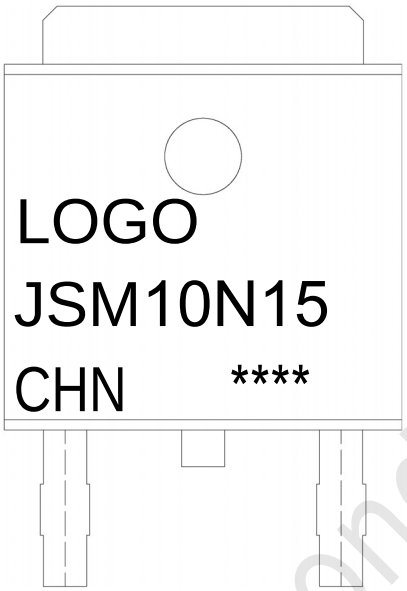


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

印章说明 / Marking Instructions



说明：

LOGO： 为公司图标

10N15 为型号代码

****： 为生产批号代码，随生产批号变化。

CHN: **中国产地**

LOGO: Company Logo

10N15 : Product Type Code.

****: Lot No. Code, code change with Lot No.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by JSMSEMI ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ AOD464 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C BSC884N03MS G BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7 BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1 IPS60R1K0PFD7SAKMA1